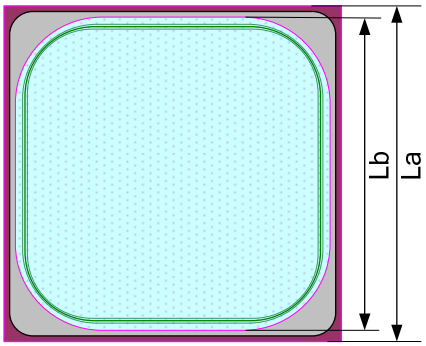
Silan
Microelectronics

2SB075030MLJL SCHOTTKY BARRIER DIODE CHIPS

DESCRIPTION

- 2SB075030MLJL is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- Low power losses, high efficiency;
- Guard ring construction for transient protection;
- Low forward voltage drop;
- High ESD capability;
- High surge capability;
- Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits.;
- Chip Size:750μm X 750μm;
- Chip Thickness: 210±20μm;



Chip Topography and Dimensions

La: Chip Size: 750μm;

Lb: Pad Size: 655μm;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB075030MLJL	For Au and AlSi wire bonding package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Average Forward Rectified Current	I_{FAV}	1.0	A
Peak Forward Surge Current@8.3ms	I_{FSM}	5.5	A
Maximum Operation Junction Temperature	T_J	125	°C
Storage Temperature Range	T_{STG}	-40~125	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	V_{BR}	I_R=100μA	30	--	V
Forward Voltage	V_{F1}	I_F=0.7A	--	0.45	V
	V_{F2}	I_F=1.0A	--	0.5	V
Reverse Current	I_R	V_R=30V	--	60	μA